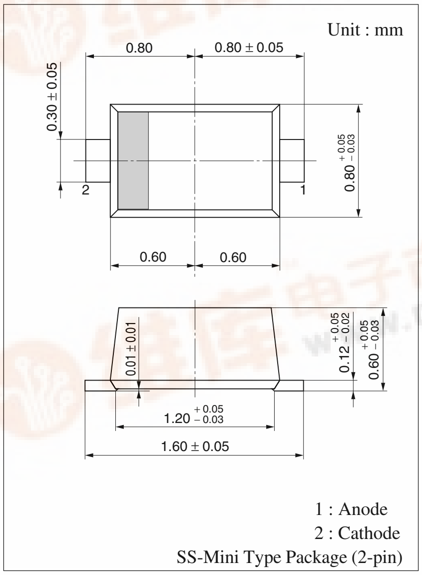
MA2SD10

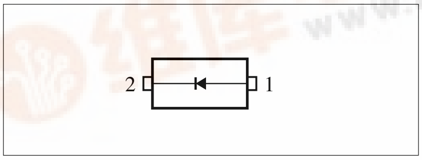
Silicon epitaxial planar type

For super-high speed switching circuit



Marking Symbol: 2L

Internal Connection



■ Features

- Sealed in the super small SS-mini type 2-pin package
- Allowing to rectify under ($I_{F(AV)}$ = 200 mA) condition
- Low forward rise voltage V_F
- Allowing high-density mounting

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	20	V
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Peak forward current	I_{FM}	300	mA
Average forward current	$I_{F(AV)}$	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55 to +125	°C

Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

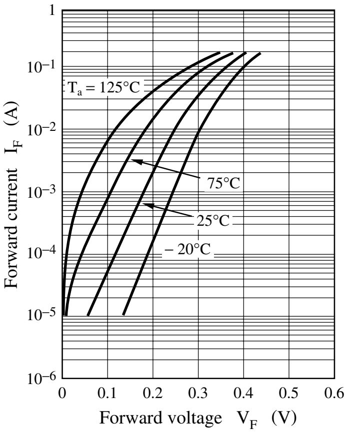
■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	V_R = 10 V			20	μA
Forward voltage (DC)	V_{F1}	I_F = 5 mA			0.27	V
	V_{F2}	I_F = 200 mA			0.47	V
Terminal capacitance	C_t	V_R = 0 V, f = 1 MHz		40		pF

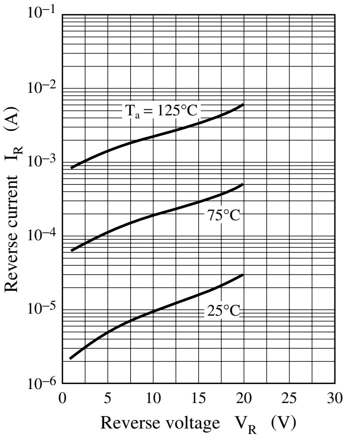
Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 250 MHz

I_F — V_F


1
10⁻¹
10⁻²
10⁻³
10⁻⁴
10⁻⁵
10⁻⁶
Forward current I_F (A)
T_a = 125°C
75°C
25°C
− 20°C
0
0.1
0.2
0.3
0.4
0.5
0.6
Forward voltage V_F (V)

I_R — V_R


10⁻¹
10⁻²
10⁻³
10⁻⁴
10⁻⁵
10⁻⁶
Reverse current I_R (A)
T_a = 125°C
75°C
25°C
0
5
10
15
20
25
30
Reverse voltage V_R (V)